

FGA15N120ANTDTU 1200 V, 15 A NPT Trench IGBT

Features

- NPT Trench Technology, Positive temperature coefficient
- Low Saturation Voltage: V_{CE(sat), typ} = 1.9 V
 Q I_C = 15 A and T_C = 25°C
- Low Switching Loss: $E_{off, typ} = 0.6 \text{ mJ}$ @ $I_C = 15 \text{ A}$ and $T_C = 25 ^{\circ}\text{C}$
- Extremely Enhanced Avalanche Capability

Description

Using Fairchild's proprietary trench design and advanced NPT technology, the 1200V NPT IGBT offers superior conduction and switching performances, high avalanche ruggedness and easy parallel operation.

This device is well suited for the resonant or soft switching application such as induction heating, microwave oven.





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit
V _{CES}	Collector-Emitter Voltage		1200	V
V _{GES}	Gate-Emitter Voltage		± 20	V
I _C	Collector Current	@ T _C = 25°C	30	A
	Collector Current	@ T _C = 100°C	15	A
I _{CM}	Pulsed Collector Current (Note 1)		45	A
	Diode Continuous Forward Current	@ T _C = 25°C	30	A
IF	Diode Continuous Forward Current	@ T _C = 100°C	15	A
I _{FM}	Diode Maximum Forward Current		45	A
D	Maximum Power Dissipation	@ T _C = 25°C	186	W
P_{D}	Maximum Power Dissipation	@ T _C = 100°C	74	W
TJ	Operating Junction Temperature		-55 to +150	°C
T _{stg}	Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for IGBT		0.67	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case for Diode		2.88	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		40	°C/W

Notes:

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity	
FGA15N120ANTDTU_F109	FGA15N120ANTDTU	TO-3P	Tube	N/A	N/A	30	

Electrical Characteristics of the IGBT $T_C = 25^{\circ}$ C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$			3	mA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}$, $V_{CE} = 0 V$			± 250	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	$I_C = 15 \text{ mA}, V_{CE} = V_{GE}$	4.5	6.5	8.5	V
V _{CE(sat)}	Collector to Emitter	I _C = 15 A, V _{GE} = 15 V		1.9	2.4	V
, ,	Saturation Voltage	$I_C = 15 \text{ A}, V_{GE} = 15 \text{ V},$ $T_C = 125^{\circ}\text{C}$		2.2		V
		$I_C = 30 \text{ A}, V_{GE} = 15 \text{ V}$		2.3		V
Dynamic C	haracteristics					
C _{ies}	Input Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$		2650		pF
C _{oes}	Output Capacitance	f = 1 MHz		143		pF
C _{res}	Reverse Transfer Capacitance			96		pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 15 \text{ A},$		15		ns
t _r	Rise Time	$R_G = 10 \Omega$, $V_{GE} = 15 V$, Inductive Load, $T_C = 25^{\circ}C$		20		ns
t _{d(off)}	Turn-Off Delay Time	madelive Edda, 16 = 28 G		160		ns
t _f	Fall Time			100	180	ns
E _{on}	Turn-On Switching Loss			3	4.5	mJ
E _{off}	Turn-Off Switching Loss		/	0.6	0.9	mJ
E _{ts}	Total Switching Loss		/	3.6	5.4	mJ
t _{d(on)}	Turn-On Delay Time	$V_{CC} = 600 \text{ V}, I_{C} = 15 \text{ A},$	/	15		ns
t _r	Rise Time	$R_G = 10 \Omega$, $V_{GE} = 15 V$, Inductive Load, $T_C = 125^{\circ}C$		20		ns
t _{d(off)}	Turn-Off Delay Time	Inductive Load, 1C = 123 C		170		ns
t _f	Fall Time			150		ns
E _{on}	Turn-On Switching Loss			3.2	4.8	mJ
E _{off}	Turn-Off Switching Loss			0.8	1.2	mJ
E _{ts}	Total Switching Loss			4.0	6.0	mJ
Qg	Total Gate Charge	$V_{CE} = 600 \text{ V}, I_{C} = 15 \text{ A},$		120	180	nC
Q _{ge}	Gate-Emitter Charge	V _{GE} = 15 V		16	22	nC
Q _{gc}	Gate-Collector Charge			50	65	nC

Electrical Characteristics of DIODE $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
V_{FM}	Diode Forward Voltage	I _F = 15 A	$T_C = 25^{\circ}C$		1.7	2.7	٧
			T _C = 125°C		1.8		
t _{rr}	Diode Reverse Recovery Time	I _F = 15 A	$T_C = 25^{\circ}C$		210	330	ns
		$di_F/dt = 200 A/\mu s$	T _C = 125°C		280		
I _{rr}	Diode Peak Reverse Recovery Cur-		$T_C = 25^{\circ}C$		27	40	Α
	rent		T _C = 125°C		31		
Q _{rr}	Diode Reverse Recovery Charge		$T_C = 25^{\circ}C$		2835	6600	nC
			T _C = 125°C		4340		

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

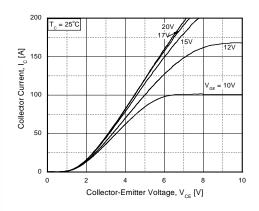


Figure 3. Saturation Voltage vs. Case
Temperature at Variant Current Level

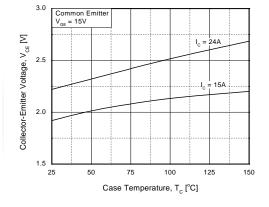


Figure 5. Saturation Voltage vs. V_{GE}

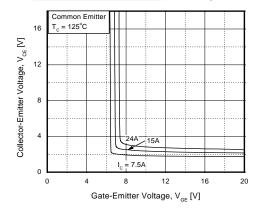


Figure 2. Typical Saturation Voltage Characteristics

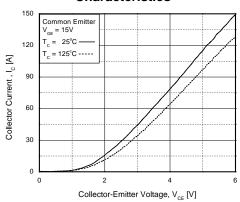


Figure 4. Saturation Voltage vs. V_{GE}

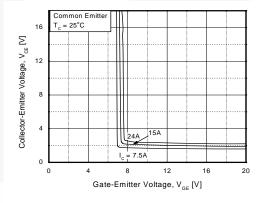
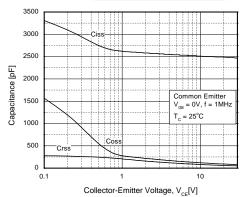


Figure 6. Capacitance Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Turn-On Characteristics vs. Gate Resistance

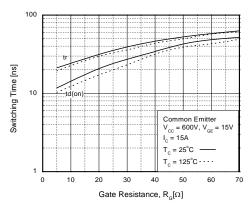


Figure 8. Turn-Off Characteristics vs. Gate Resistance

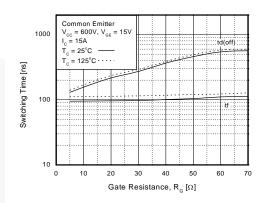


Figure 9. Switching Loss vs. Gate Resistance

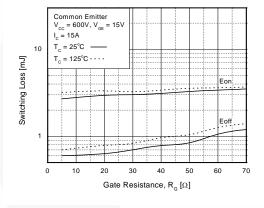


Figure 10. Turn-On Characteristics vs. Collector Current

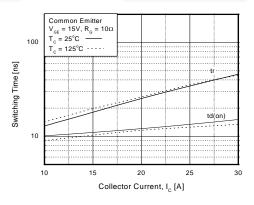


Figure 11. Turn-Off Characteristics vs.
Collector Current

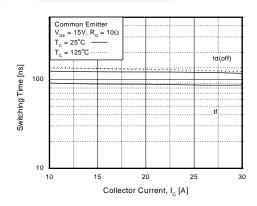
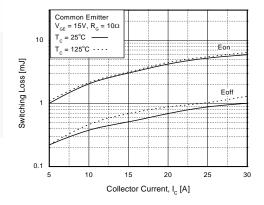


Figure 12. Switching Loss vs. Collector Current



Typical Performance Characteristics (Continued)

Figure 13. Gate Charge Characteristics

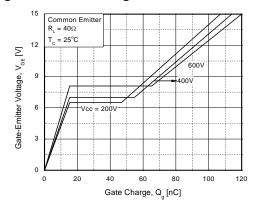


Figure 14. SOA Characteristics

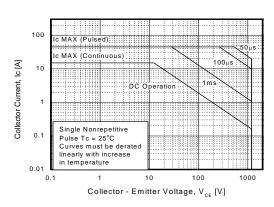


Figure 15. Turn-Off SOA

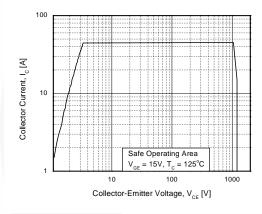
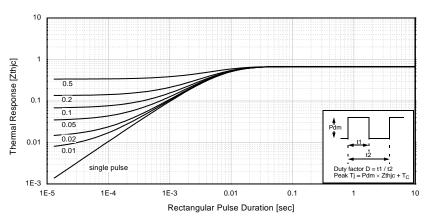


Figure 16. Transient Thermal Impedance of IGBT



Typical Performance Characteristics (Continued)

Figure 17. Forward Characteristics

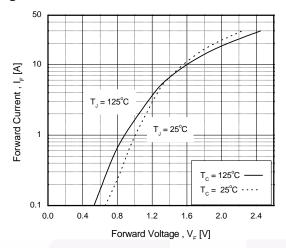


Figure 19. Stored Charge

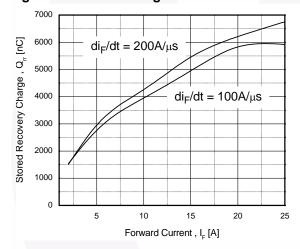


Figure 18. Reverse Recovery Current

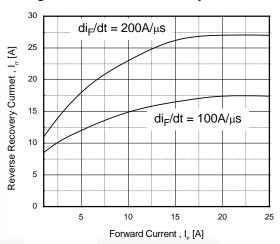
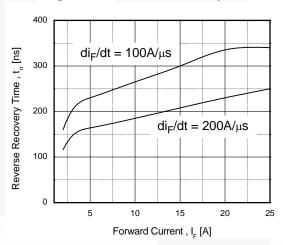


Figure 20. Reverse Recovery Time



Mechanical Dimensions

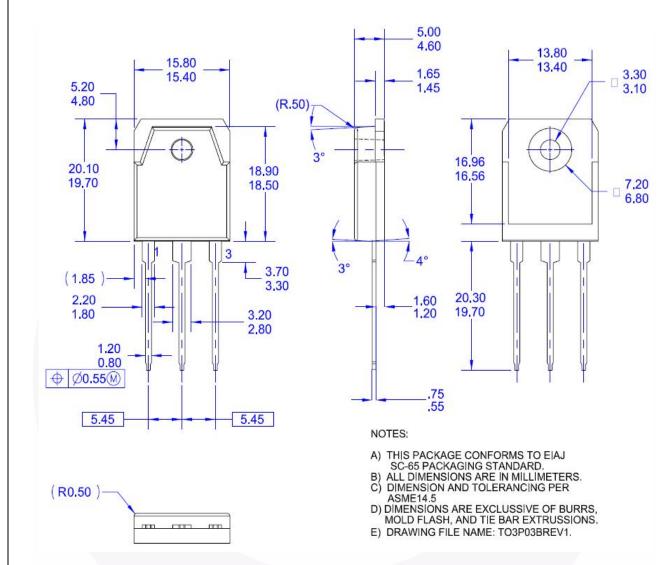


Figure 21. TO-3P 3L - 3LD, T03, PLASTIC, EIAJ SC-65

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Rev. 166